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Dopant Diffusion Barrier Layer And Method Of ManufactureABSTRACT

The present invention relates to a multi-layer dopant barrier and its method of fabrication for use in semiconductor structures. In an illustrative embodiment, the multi-layer dopant barrier is disposed between a first doped layer and a second doped layer. The multi-layer dopant barrier further includes a first dopant blocking layer adjacent the first doped layer and a second dopant blocking layer adjacent the second doped layer. A technique for fabricating the multi layer dopant barrier is disclosed. A first dopant blocking layer is formed at a first temperature, and a second dopant blocking layer is formed at a second temperature over the first barrier layer.

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